



2815

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

## Applicant:

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I hereby certify that this correspondence is being faxed to the United States Postal Service at (703) 872-9318 on November 27, 2002 and mailed first class mail in an envelope addressed to: Commissioner of Patents and Trademarks Washington, D.C. 20231 on December 2, 2002.

MARY V. CARTON  
Printed name of person mailing paper or fee  
Signature of person mailing paper or fee

Case: 1-10-31

Serial No.: 09/464,811

Group Art Unit: 2815

Filed: December 17, 1999

Examiner: L. Cruz

Title: Integration of Low Dielectric Material in Semiconductor Circuit S  
Structures

## AMENDMENT

Assistant Commissioner of Patents  
Washington, D.C. 20231

SIR:

In response to the office action of November 1, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

22. (Amended) A method for forming a semiconductor structure,  
comprising:

depositing a first insulative layer over a semiconductor layer;

forming a lower level of interconnect members over the first insulative layer;

C1 depositing a second insulative layer between and over the lower level of interconnect  
members;

forming an upper level of interconnect members over the second insulative layer

removing portions of the second insulative layer positioned between interconnect  
members of the lower and upper levels; and

forming a third insulative layer in regions from which the second  
insulative layer is removed.

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1-8-03  
Jen.